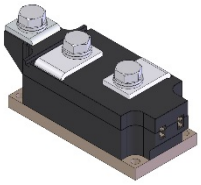
IXYS



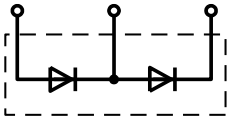
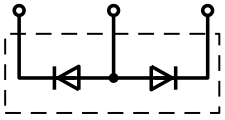
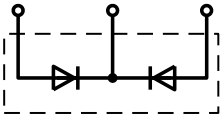
Date: 4th March, 2016

Data Sheet Issue: 3

Dual Diode Modules

MD#630-30N2 & MD#630-36N2

Absolute Maximum Ratings

V_{RRM} [V]	 MDD	 MDA	 MDK
3000	630-30N2	630-30N2	630-30N2
3600	630-36N2	630-36N2	630-36N2

	VOLTAGE RATINGS	MAXIMUM LIMITS	UNITS
V_{RRM}	Repetitive peak reverse voltage [1]	3000-3600	V
V_{RSM}	Non-repetitive peak reverse voltage [1]	3100-3700	V

	OTHER RATINGS	MAXIMUM LIMITS	UNITS
$I_{F(AV)M}$	Maximum average on-state current, T_C = 85°C [2]	630	A
$I_{F(AV)M}$	Maximum average on-state current. T_C = 100°C [2]	530	A
$I_{F(RMS)M}$	Nominal RMS on-state current, T_C = 55°C [2]	1275	A
$I_{F(d.c.)}$	D.C. on-state current, T_C = 55°C	1090	A
I_{FSM}	Peak non-repetitive surge t_p = 10 ms, V_{RM} = 60%V_{RRM} [3]	11.7	kA
I_{FSM2}	Peak non-repetitive surge t_p = 10 ms, $V_{RM} \leq$ 10V [3]	13.0	kA
I^2t	I^2t capacity for fusing t_p = 10 ms, V_{RM} = 60%V_{RRM} [3]	684×10^3	A^2s
I^2t	I^2t capacity for fusing t_p = 10 ms, $V_{RM} \leq$ 10 V [3]	845×10^3	A^2s
V_{ISOL}	Isolation Voltage [4]	3000	V
	Isolation Voltage – Enhanced. See order code page 9 [4]	5000	V
$T_{vj\ op}$	Operating temperature range	-40 to +150	°C
T_{stg}	Storage temperature range	-40 to +150	°C

Notes:

1) De-rating factor of 0.13% per °C is applicable for T_{vj} below 25°C.
2) Single phase; 50 Hz, 180° half-sinewave.
3) Half-sinewave, 150°C T_{vj} initial.
4) AC RMS voltage, 50 Hz, 1min test

Characteristics

	PARAMETER	MIN.	TYP.	MAX.	TEST CONDITIONS [1]	UNITS
V_{FM}	Maximum peak forward voltage	-	-	1.20	I_{FM} = 800 A	V
V_{FM}	Maximum peak forward voltage	-	-	1.80	I_{FM} = 2000 A	V
V_{T0}	Threshold voltage	-	-	0.80		V
r_T	Slope resistance	-	-	0.50		mΩ
I_{RRM}	Peak reverse current	-	-	50	Rated V_{RRM}	mA
Q_{rr}	Recovered Charge	-	2900	3200	I_{TM} = 500A, t_p =1ms, di/dt =10A/µs, V_R =100 V	µC
Q_{ra}	Recovered Charge, 50% chord	-	2560	-		µC
I_{rm}	Reverse recovery current	-	150	-		A
t_{rr}	Reverse recovery time, 50% chord	-	34	-		µs
R_{thJC}	Thermal resistance, junction to case	-	-	0.0650	Single Diode	K/W
		-	-	0.0325	Whole Module	K/W
R_{thCH}	Thermal resistance, case to heatsink	-	-	0.02	Single Diode	K/W
		-	-	0.01	Whole Module	K/W
F_1	Mounting force (to heatsink) [2]	5.1	-	6.9		Nm
F_2	Mounting force (to terminals) [2]	10.2	-	13.8		Nm
W_t	Weight	-	1.5	-		kg

Notes:

1) Unless otherwise indicated T_{vj}=150°C.
2) Screws must be lubricated.

Notes on Ratings and Characteristics

1.0 Voltage Grade Table

Voltage Grade	V_{RRM} V	V_{RSM} V	V_R DC V
3000	3000	3100	2250
3600	3600	3700	2700

2.0 Extension of Voltage Grades

This report is applicable to other voltage grades when supply has been agreed by Sales/Production.

3.0 De-rating Factor

A blocking voltage de-rating factor of 0.13%/°C is applicable to this device for T_{vj} below 25°C.

4.0 Snubber Components

When selecting snubber components, care must be taken not to use excessively large values of snubber capacitor or excessively small values of snubber resistor. Such excessive component values may lead to device damage due to the large resultant values of snubber discharge current. If required, please consult the factory for assistance.

5.0 Computer Modelling Parameters

5.1 Thyristor Dissipation Calculations

$$I_{AV} = \frac{-V_{T0} + \sqrt{V_{T0}{}^2 + 4 \cdot ff^2 \cdot r_T \cdot W_{AV}}}{2 \cdot ff^2 \cdot r_T}$$

and:

$$W_{AV} = \frac{\Delta T}{R_{th}}$$

$$\Delta T = T_{j\max} - T_K$$

Where V_{T0} = 0.80 V, r_T = 0.50 mΩ.

R_{th} = Supplementary thermal impedance, see table below and

ff = Form factor, see table below.

Supplementary Thermal Impedance							
Conduction Angle	30°	60°	90°	120°	180°	270°	d.c.
Square wave	0.0798	0.0742	0.0712	0.0694	0.0674	0.0659	0.0650
Sine wave	0.0736	0.0685	0.0667	0.0657	0.0651		

Form Factors							
Conduction Angle	30°	60°	90°	120°	180°	270°	d.c.
Square wave	3.464	2.449	2	1.732	1.414	1.149	1
Sine wave	3.98	2.778	2.22	1.879	1.57		

5.2 Calculating diode V_F using ABCD Coefficients

The forward characteristic I_F vs. V_F, on page 6 is represented by a set of constants A, B, C, D, forming the coefficients of the representative equation for V_F in terms of I_F given below:

$$V_F = A + B \cdot \ln(I_F) + C \cdot I_F + D \cdot \sqrt{I_F}$$

The constants, derived by curve fitting software, are given below for both hot and cold characteristics. The resulting values for V_F agree with the true device characteristic over a current range, which is limited to that plotted.

25°C Coefficients		150°C Coefficients	
A	0.8507456	A	0.4945386
B	0.04762876	B	0.05726181
C	4.08857×10^{-4}	C	4.98169×10^{-4}
D	-3.12768×10^{-3}	D	-2.79389×10^{-3}

5.3 D.C. Thermal Impedance Calculation

$$r_t = \sum_{p=1}^{p=n} r_p \cdot \left(1 - e^{\frac{-t}{\tau_p}}\right)$$

Where *p = 1* to *n and:*

n = number of terms in the series
t = Duration of heating pulse in seconds
r_t = Thermal resistance at time t
r_p = Amplitude of p_{th} term
τ_p = Time Constant of r_{th} term

The coefficients for this device are shown in the table below:

D.C. Single Diode				
Term	1	2	3	4
r_p	0.03671713	0.01198766	0.01439901	1.895749×10^{-3}
τ_p	3.123905	0.8540715	0.1955971	1.412289×10^{-3}

6.0 Reverse recovery ratings

(i) Q_{ra} is based on 50% I_{RM} chord as shown in Fig. 1

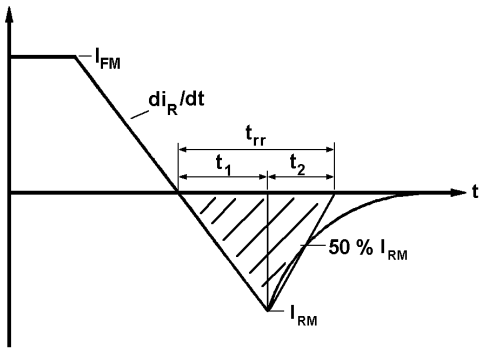


Fig. 1

(ii) Q_{rr} is based on a 150 μs integration time i.e.

$$Q_{rr} = \int_0^{150\mu s} i_{rr}.dt$$

(iii)

$$K\ Factor = \frac{t_1}{t_2}$$

Curves

Figure 1 – Forward characteristics of Limit device

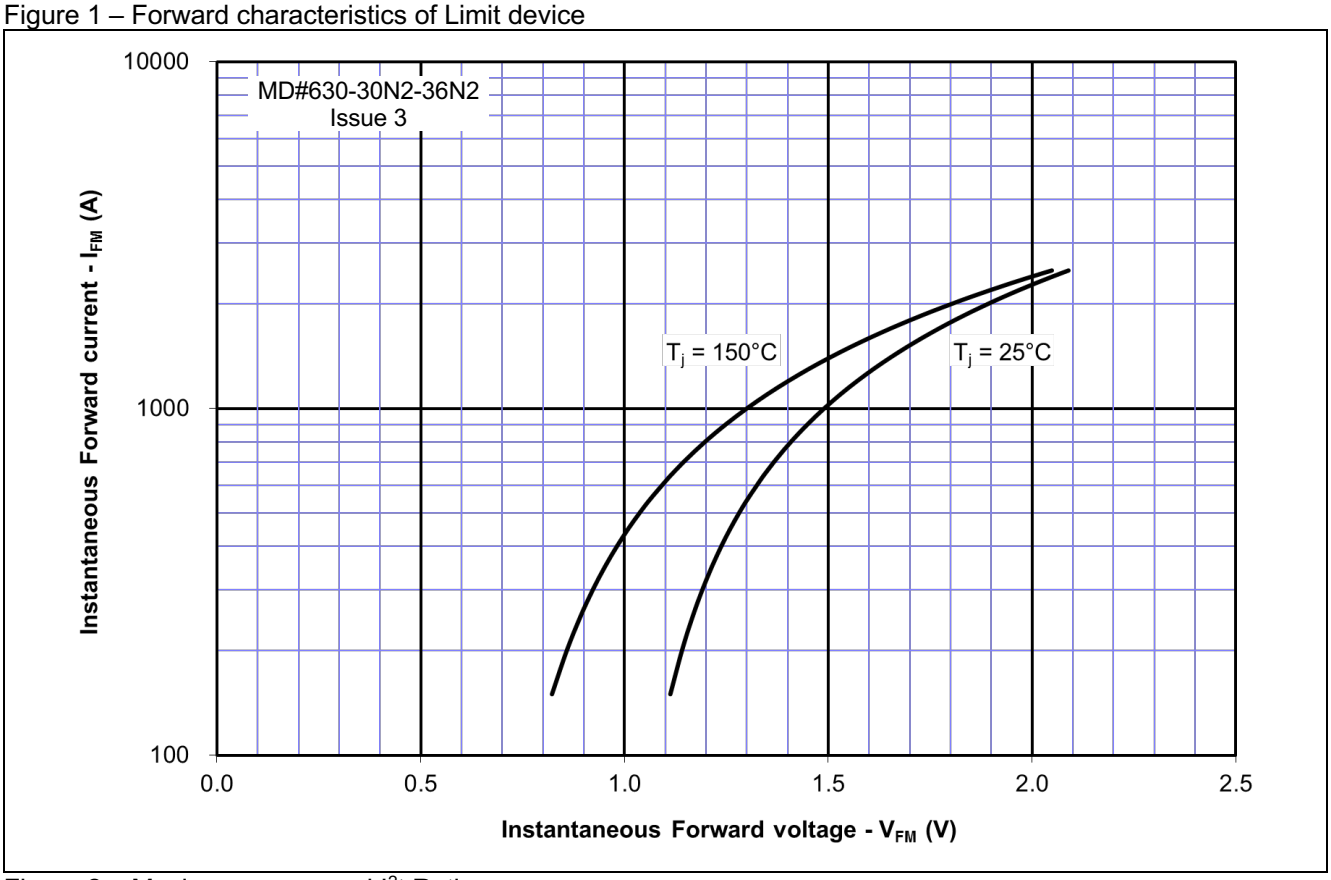


Figure 2 – Maximum surge and I^2t Ratings

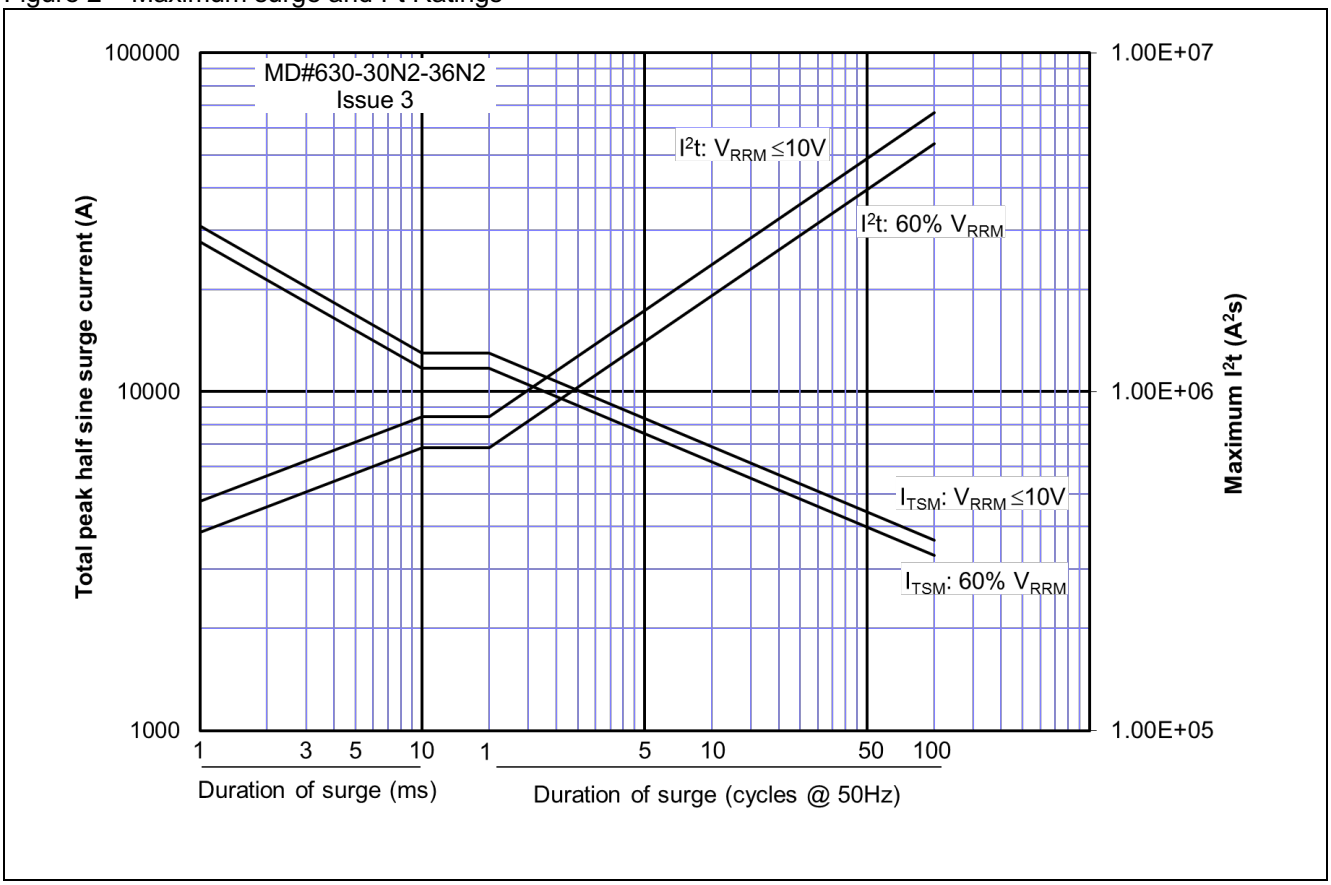


Figure 3 - Total recovered charge, Q_{rr}

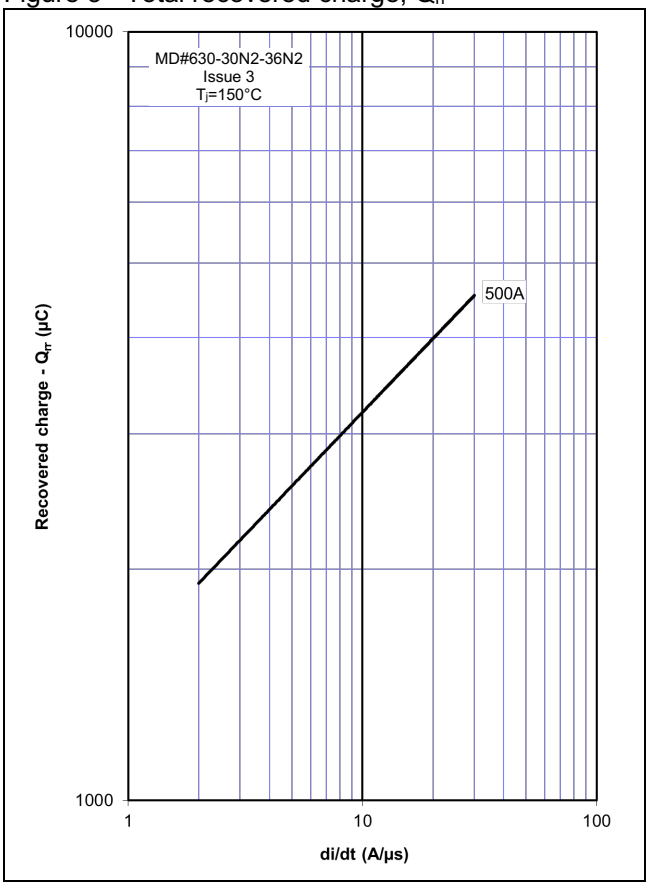


Figure 4 - Recovered charge, Q_{ra} (50% chord)

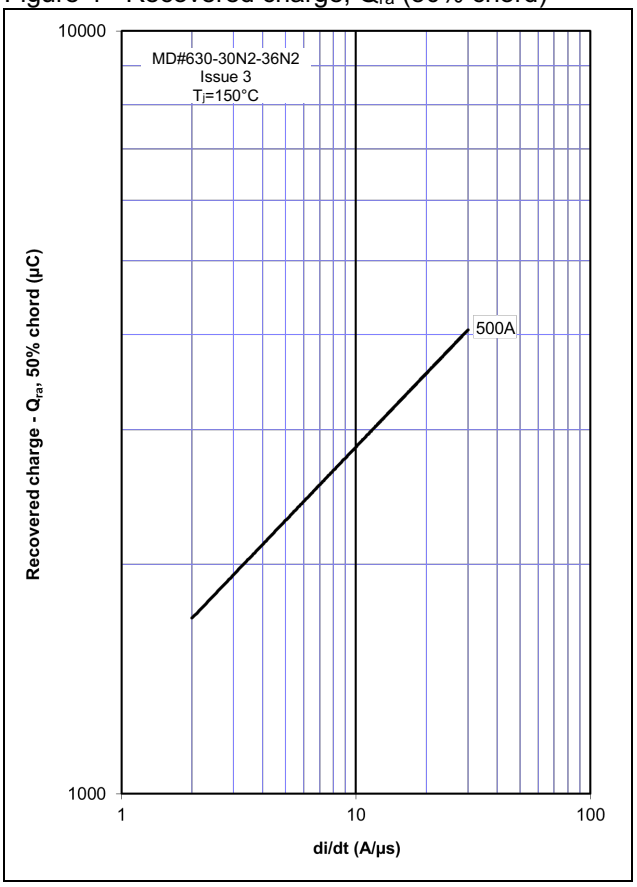


Figure 5 - Peak reverse recovery current, I_{rm}

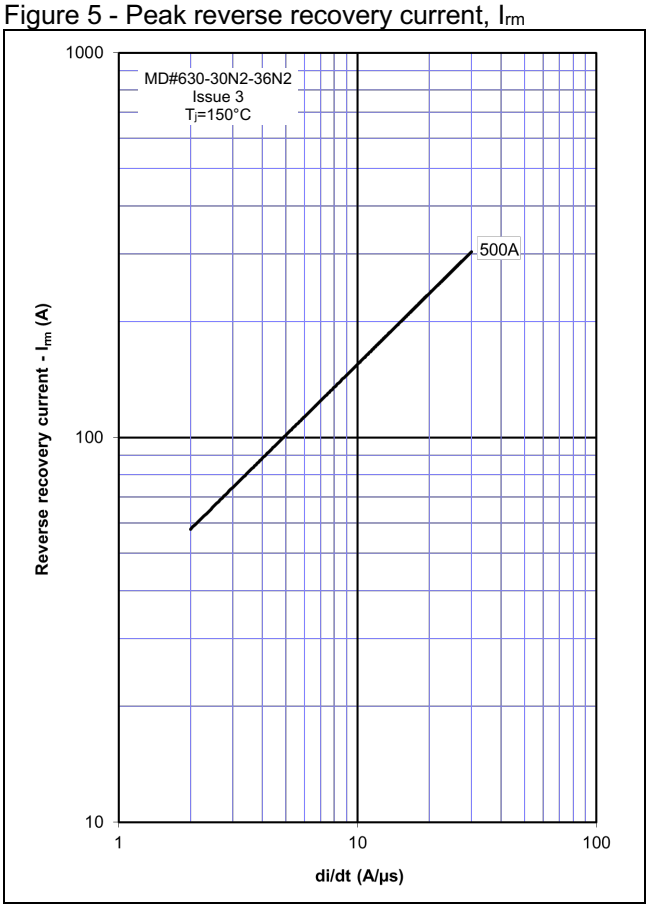


Figure 6 - Maximum recovery time, t_{rr} (50% chord)

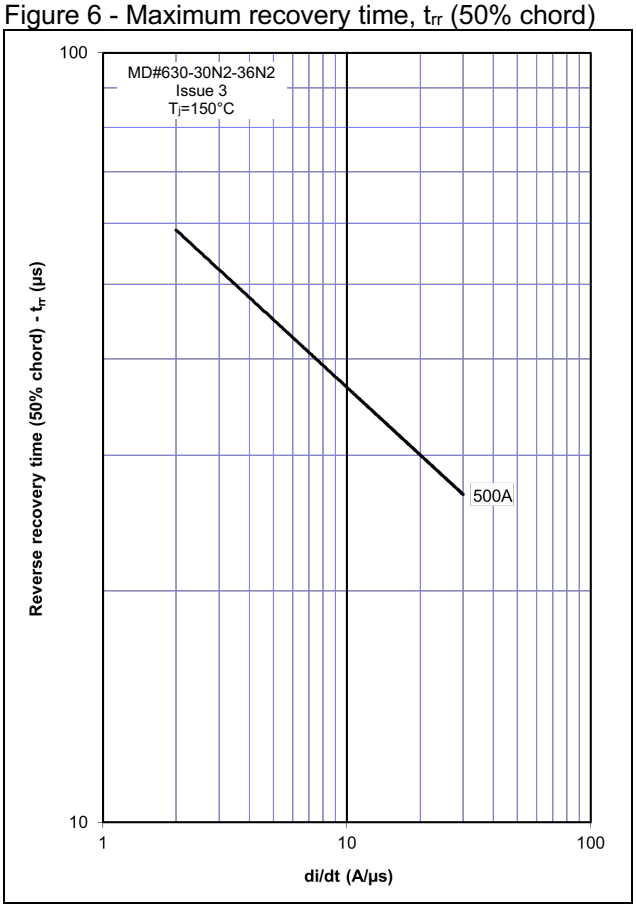


Figure 7 – Forward current vs. Power dissipation

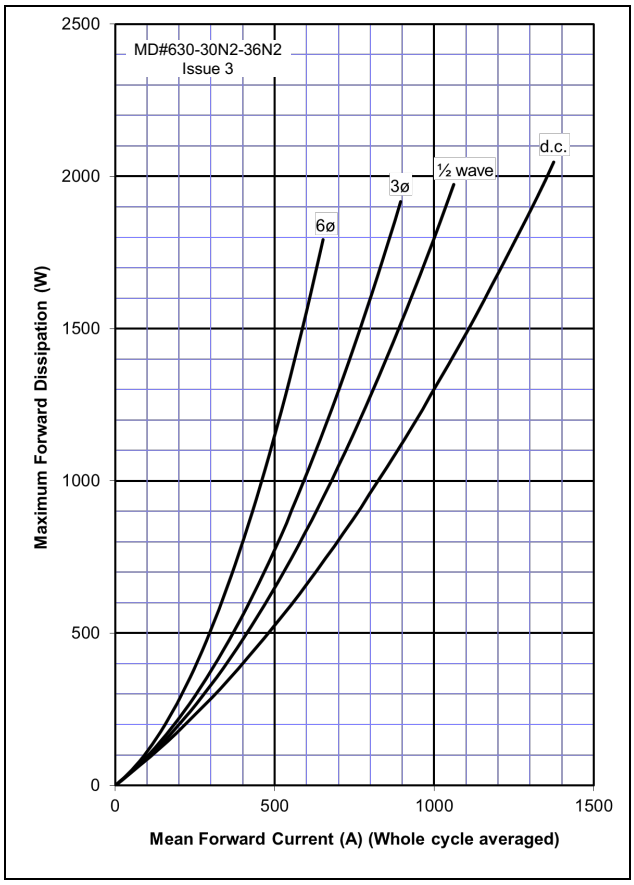


Figure 8 – Forward current vs. Heatsink temperature

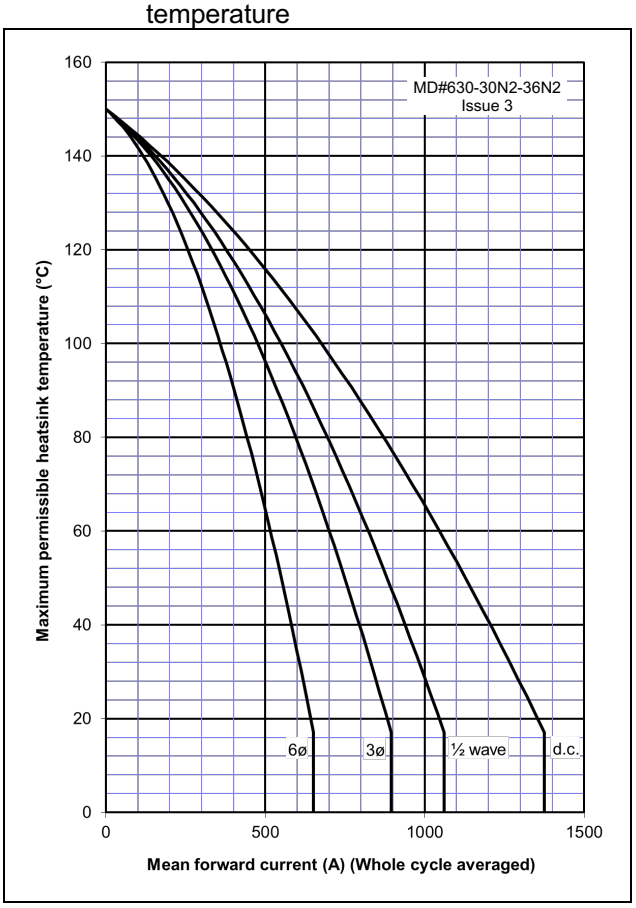
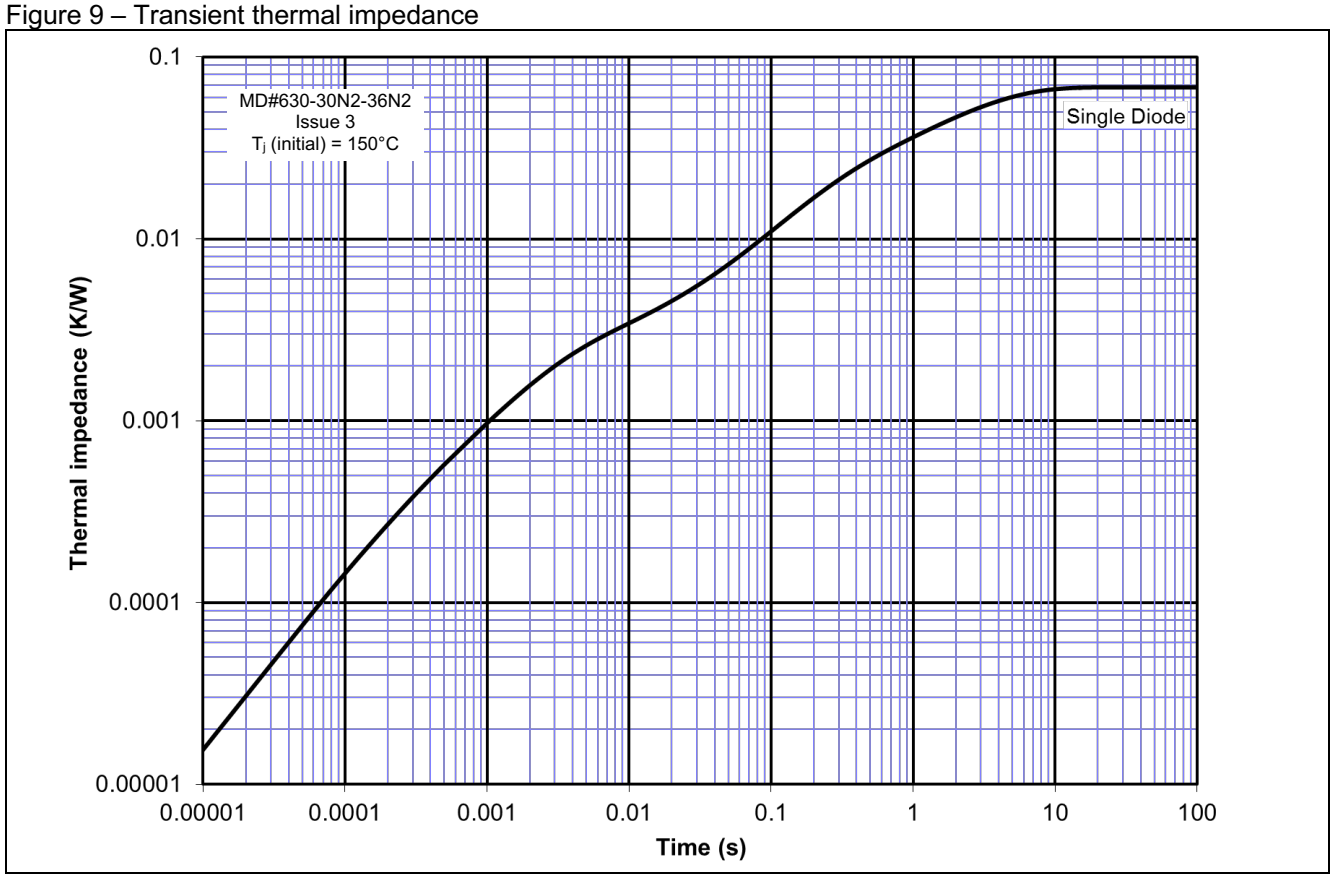
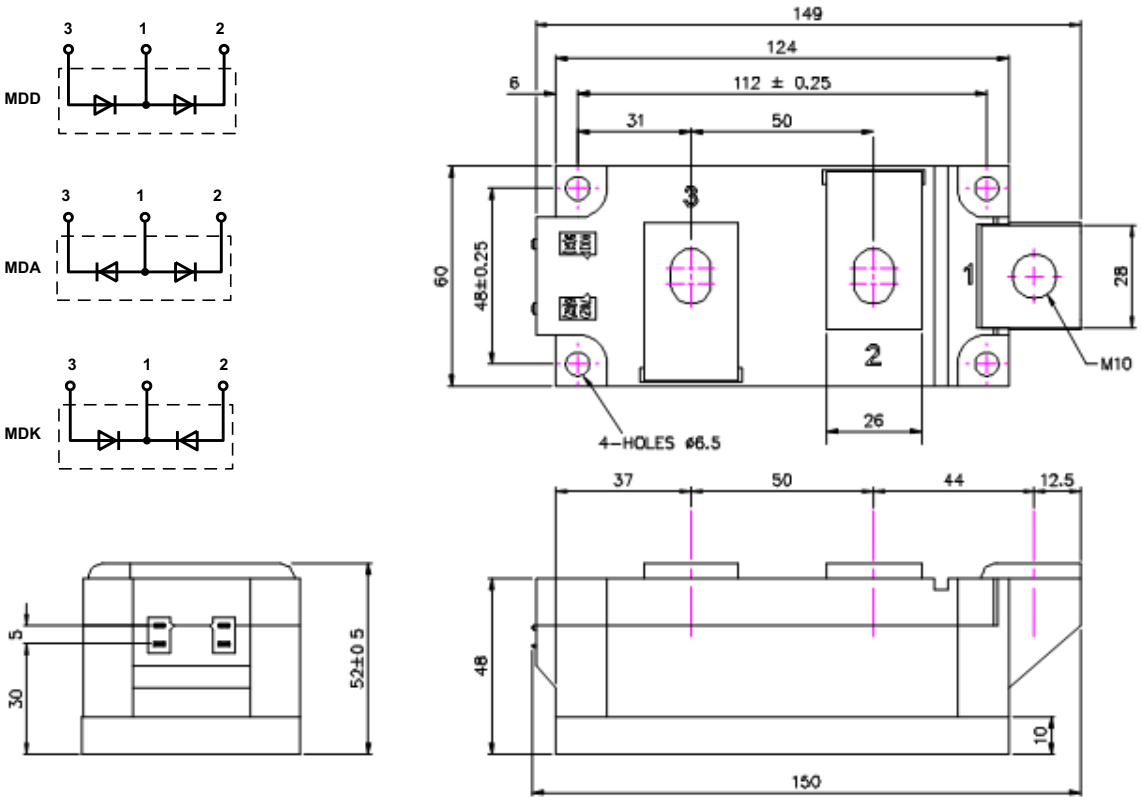


Figure 9 – Transient thermal impedance



Outline Drawing & Ordering Information



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ORDERING INFORMATION (Please quote 11/14 digit code as below)

M	D#	630	♦♦	N	2	HAD
Fixed Type Code	Configuration Code DD, DA, DK	Fixed Type Code	Voltage code V_{RRM}/100 30-36	Standard Diode	Fixed Version Code	Optional for Enhanced 5kV Isolation Voltage

Typical order code: MDA630-36N2– MDA configuration, 3600V V_{RRM}

Typical order code (Enhanced Isolation): MDA630-36N2HAD– MDA configuration, 3600V V_{RRM}, 5kV isolation

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